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# **Octal Bus Buffer**

# Inverting

The MC74LVX540 is an advanced high speed CMOS inverting octal bus buffer fabricated with silicon gate CMOS technology. It achieves high speed operation similar to equivalent Bipolar Schottky TTL while maintaining CMOS low power dissipation.

The MC74LVX540 features inputs and outputs on opposite sides of the package and two AND–ed active–low output enables. When either  $\overline{OE1}$  or  $\overline{OE2}$  are high, the terminal outputs are in the high impedance state.

The internal circuit is composed of three stages, including a buffer output which provides high noise immunity and stable output. The inputs tolerate voltages up to 7.0 V, allowing the interface of 5.0 V systems to 3.0 V systems.

# Features

- High Speed:  $t_{PD} = 5.0$  ns (Typ) at  $V_{CC} = 3.3$  V
- Low Power Dissipation:  $I_{CC} = 4 \ \mu A$  (Max) at  $T_A = 25^{\circ}C$
- High Noise Immunity:  $V_{NIH} = V_{NIL} = 28\% V_{CC}$
- Power Down Protection Provided on Inputs
- Balanced Propagation Delays
- Designed for 2.0 V to 3.6 V Operating Range
- Low Noise:  $V_{OLP} = 1.2 V (Max)$
- Pin and Function Compatible with Other Standard Logic Families
- Latchup Performance Exceeds 300 mA
- Chip Complexity: 124 FETs or 31 Equivalent Gates
- ESD Performance:

Human Body Model > 2000 V; Machine Model > 200 V

• Pb–Free Packages are Available\*



## ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 3 of this data sheet.

\*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.





OE1	1●	20	] V <sub>CC</sub>
A1 [	2	19	] <u>0E2</u>
A2 [	3	18	] <u>71</u>
A3 [	4	17	] <u>72</u>
A4 [	5	16	] <u>73</u>
A5 [	6	15	] <u>74</u>
A6 [	7	14	] <u>Y5</u>
A7 [	8	13	] <u>Y6</u>
A8 [	9	12	] <u>77</u>
GND [	10	11	] <u>78</u>

Figure 2. PIN ASSIGNMENT



Figure 3. IEC LOGIC DIAGRAM

## **FUNCTION TABLE**

	Inputs		Output Y	
OE1	OE2	Α	Output	
L	L	L	н	
L L	L	н	L	
н	Х	Х	Z	
X	Н	Х	Z	

# MAXIMUM RATINGS

Symbol	Paramete	r	Value	Unit
V <sub>CC</sub>	DC Supply Voltage		- 0.5 to + 7.0	V
V <sub>in</sub>	DC Input Voltage		- 0.5 to + 7.0	V
V <sub>out</sub>	DC Output Voltage		-0.5 to V <sub>CC</sub> + 0.5	V
I <sub>IK</sub>	Input Diode Current		-20	mA
I <sub>ОК</sub>	Output Diode Current		±20	mA
I <sub>out</sub>	DC Output Current, per Pin		±25	mA
I <sub>CC</sub>	DC Supply Current, $V_{CC}$ and G	ND Pins	±75	mA
PD	Power Dissipation in Still Air,	SOIC Packages† TSSOP Package†	500 450	mW
T <sub>stg</sub>	Storage Temperature		– 65 to + 150	°C

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

†Derating — SOIC Packages: - 7 mW/°C from 65° to 125°C

TSSOP Package: - 6.1 mW/°C from 65° to 125°C

## **RECOMMENDED OPERATING CONDITIONS**

Symbol	Parameter	Min	Max	Unit
V <sub>CC</sub>	DC Supply Voltage	2.0	3.6	V
V <sub>in</sub>	DC Input Voltage	0	5.5	V
V <sub>out</sub>	DC Output Voltage	0	V <sub>CC</sub>	V
T <sub>A</sub>	Operating Temperature, All Package Types	-40	+85	°C
t <sub>r</sub> , t <sub>f</sub>	Input Rise and Fall Time V <sub>CC</sub> = 3.3 V $\pm$ 0.3 V (See Figure 4)	0	100	ns/V

#### **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>
MC74LVX540M	SOEIAJ-20	50 Units / Rail
MC74LVX540MG	SOEIAJ-20 (Pb-Free)	50 Units / Rail
MC74LVX540MEL	SOEIAJ-20	2000 Tape & Reel
MC74LVX540MELG	SOEIAJ-20 (Pb-Free)	2000 Tape & Reel

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high–impedance circuit. For proper operation, V<sub>in</sub> and V<sub>out</sub> should be constrained to the range GND  $\leq$  (V<sub>in</sub> or V<sub>out</sub>)  $\leq$  V<sub>CC</sub>. Unused inputs must always be

This device contains protection

tied to an appropriate logic voltage level (e.g., either GND or  $V_{CC}$ ). Unused outputs must be left open.

## DC ELECTRICAL CHARACTERISTICS

			v <sub>cc</sub>	T <sub>A</sub> = 25°C		$T_A = -40$	D to 85°C		
Symbol	Parameter	Test Conditions	V	Min	Тур	Max	Min	Max	Unit
V <sub>IH</sub>	Minimum High-Level Input Voltage		2.0 3.0 3.6	1.50 2.0 2.4			1.50 2.0 2.4		V
V <sub>IL</sub>	Maximum Low-Level Input Voltage		2.0 3.0 3.6			0.50 0.80 0.80		0.50 0.80 0.80	V
V <sub>OH</sub>		$I_{OH} = -50 \ \mu A$ $I_{OH} = -50 \ \mu A$ $I_{OH} = -4 \ m A$	2.0 3.0 3.0	1.9 2.9 2.58	2.0 3.0		1.9 2.9 2.48		V
V <sub>OL</sub>	Maximum Low–Level Output Voltage $V_{in} = V_{IH}$ or $V_{IL}$	$I_{OL} = 50 \ \mu A$ $I_{OL} = 50 \ \mu A$ $I_{OL} = 4 \ m A$	2.0 3.0 3.0		0.0 0.0	0.1 0.1 0.36		0.1 0.1 0.44	V
l <sub>in</sub>	Maximum Input Leakage Current	V <sub>in</sub> = 5.5 V or GND	0 to 3.6			±0. 1		± 1.0	μΑ
l <sub>oz</sub>	Maximum 3–State Leakage Current	$V_{in} = V_{IL} \text{ or } V_{IH}$ $V_{out} = V_{CC} \text{ or } GND$	3.6			±0. 25		±2.5	μΑ
I <sub>CC</sub>	Maximum Quiescent Supply Current	$V_{in} = V_{CC} \text{ or } GND$	3.6			4.0		40.0	μΑ

# AC ELECTRICAL CHARACTERISTICS (Input t<sub>r</sub> = t<sub>f</sub> = 3.0 ns)

				T <sub>A</sub> = 25°C		$T_A = -40$	) to 85°C		
Symbol	Parameter	Test Cond	litions	Min	Тур	Max	Min	Max	Unit
t <sub>PLH</sub> , t <sub>PHL</sub>	Maximum Propagation Delay, A to $\overline{Y}$	V <sub>CC</sub> = 2.7 V	C <sub>L</sub> = 15 pF C <sub>L</sub> = 50 pF		6.2 8.5	11.3 14.9	1.0 1.0	13.5 17.0	ns
	(Figures 4 and 6)	$V_{CC} = 3.3 \pm 0.3 V$	C <sub>L</sub> = 15 pF C <sub>L</sub> = 50 pF		5.0 6.8	7.0 10.5	1.0 1.0	8.5 12.0	
t <sub>PZL</sub> , t <sub>PZH</sub>	t <sub>PZH</sub> OEn to Y	$V_{CC} = 2.7 V$ $R_L = 1 k\Omega$	C <sub>L</sub> = 15 pF C <sub>L</sub> = 50 pF		9.5 11.2	13.8 17.3	1.0 1.0	16.5 20.0	ns
(Figures 5 and 7)	$\begin{array}{l} V_{CC} = 3.3  \pm  0.3 \; V \\ R_{L} = 1k \; \Omega \end{array}$	C <sub>L</sub> = 15 pF C <sub>L</sub> = 50 pF		7.0 8.8	10.5 14.0	1.0 1.0	12.5 16.0		
t <sub>PLZ</sub> , t <sub>PHZ</sub>	Output Disable Time, OEn to Y	$V_{CC} = 2.7 V$ R <sub>L</sub> = 1 k $\Omega$	C <sub>L</sub> = 50 pF		9.8	17.9	1.0	20.0	ns
	(Figures 5 and 7)	$V_{CC} = 3.3 \pm 0.3 \text{ V}$ $R_{L} = 1 \text{ k}\Omega$	C <sub>L</sub> = 50 pF		8.7	15.4	1.0	17.5	
t <sub>OSLH</sub> , t <sub>OSHL</sub>	Output to Output Skew	V <sub>CC</sub> = 2.7 V (Note 1)	C <sub>L</sub> = 50 pF			1.5		1.5	ns
		$V_{CC} = 3.3 \pm 0.3 V$ (Note 1)	C <sub>L</sub> = 50 pF			1.5		1.5	ns
C <sub>in</sub>	Maximum Input Capacitance				4	10		10	pF
C <sub>out</sub>	Maximum Three–State Output Capacitance (Output in High Impedance State)				6				pF

		Typical @ 25°C, $V_{CC}$ = 5.0 V	
C <sub>PD</sub> Power Di	ssipation Capacitance (Note 2)	17	pF

Parameter guaranteed by design. t<sub>OSLH</sub> = |t<sub>PLHm</sub> - t<sub>PLHn</sub>|, t<sub>OSHL</sub> = |t<sub>PHLm</sub> - t<sub>PHLn</sub>|.
 C<sub>PD</sub> is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: I<sub>CC(OPR)</sub> = C<sub>PD</sub> • V<sub>CC</sub> • f<sub>in</sub> + I<sub>CC</sub>/8 (per bit). C<sub>PD</sub> is used to determine the no–load dynamic power consumption; P<sub>D</sub> = C<sub>PD</sub> • V<sub>CC</sub><sup>2</sup> • f<sub>in</sub> + I<sub>CC</sub> • V<sub>CC</sub>.

# **NOISE CHARACTERISTICS** (Input $t_f = t_f = 3.0 \text{ ns}$ , $C_L = 50 \text{ pF}$ , $V_{CC} = 3.3 \text{ V}$ )

		T <sub>A</sub> = 25°C		
Symbol	Parameter	Тур	Max	Unit
V <sub>OLP</sub>	Quiet Output Maximum Dynamic V <sub>OL</sub>	0.5	0.8	V
V <sub>OLV</sub>	Quiet Output Minimum Dynamic V <sub>OL</sub>	-0.5	-0.8	V
V <sub>IHD</sub>	Minimum High Level Dynamic Input Voltage		2.0	V
V <sub>ILD</sub>	Maximum Low Level Dynamic Input Voltage		0.8	V

SWITCHING WAVEFORMS





Figure 4.

TEST CIRCUITS







Figure 7.



Figure 8. INPUT EQUIVALENT CIRCUIT

# PACKAGE DIMENSIONS

SOIC-20 **DW SUFFIX** CASE 751D-05 **ISSUE G** 



NOTES:

- 1. 2.
- DIMENSIONS ARE IN MILLIMETERS. INTERPRET DIMENSIONS AND TOLERANCES PER ASME Y14.5M, 1994.
- DIMENSIONS D AND E DO NOT INCLUDE MOLD 3. PROTRUSION.
- MAXIMUM MOLD PROTRUSION 0.15 PER SIDE. DIMENSION B DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE PROTRUSION SHALL BE 0.13 TOTAL IN EXCESS OF B 5. DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIMETERS			
DIM	MIN	MAX		
Α	2.35	2.65		
A1	0.10	0.25		
В	0.35	0.49		
С	0.23	0.32		
D	12.65	12.95		
E	7.40	7.60		
е	1.27	BSC		
Н	10.05	10.55		
h	0.25	0.75		
L	0.50	0.90		
θ	0 °	7 °		

TSSOP-20 DT SUFFIX CASE 948E-02 ISSUE B



NOTES:

DITES:
 DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 CONTROLLING DIMENSION: MILLIMETER.
 DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS. SHALL NOT EXCEED 0.15 (0.006) PER SUDE

SIDE. 4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER

SIDE. 5. DIMENSION K DOES NOT INCLUDE 5. DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K
 DIMENSION AT MAXIMUM MATERIAL
 CONDITION.
 6. TERMINAL NUMBERS ARE SHOWN

FOR REFERENCE ONLY. 7. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE -W-. 7

	MILLIN	IETERS	INC	HES	
DIM	MIN	MAX	MIN	MAX	
Α	6.40	6.60	0.252	0.260	
В	4.30	4.50	0.169	0.177	
С		1.20		0.047	
D	0.05	0.15	0.002	0.006	
F	0.50	0.75	0.020	0.030	
G	0.65	BSC	0.026 BSC		
Н	0.27	0.37	0.011	0.015	
J	0.09	0.20	0.004	0.008	
J1	0.09	0.16	0.004	0.006	
K	0.19	0.30	0.007	0.012	
K1	0.19	0.25	0.007	0.010	
L	6.40	BSC	0.252	BSC	
Μ	0°	8°	0 °	8°	

# PACKAGE DIMENSIONS

SOEIAJ-20 **M SUFFIX** CASE 967-01 ISSUE O



<u>|</u>| <u>|</u> 10

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DETAIL P



- NOTES:
  DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
  CONTROLLING DIMENSION: MILLIMETER.
  DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH OR PROTRUSIONS AND ARE MEASURED AT THE PARTING LINE. MOLD FLASH OR PROTRUSIONS SHALL NOT EXCEED 0.15 (0.006) PER SUDE
- PROTRUSIONS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
  TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
  THE LEAD WIDTH DIMENSION (b) DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE LEAD WIDTH DIMENSION AT MAXIMUM MATERIAL CONDITION. DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OR THE FOOT. MINIMUM SPACE BETWEEN PROTRUSIONS AND ADJACENT LEAD TO BE 0.46 (0.018).

	MILLIN	IETERS	INC	HES
DIM	MIN	MAX	MIN	MAX
Α		2.05		0.081
A <sub>1</sub>	0.05	0.20	0.002	0.008
b	0.35	0.50	0.014	0.020
C	0.18	0.27	0.007	0.011
D	12.35	12.80	0.486	0.504
Е	5.10	5.45	0.201	0.215
е	1.27	BSC	0.050	BSC
HE	7.40	8.20	0.291	0.323
L	0.50	0.85	0.020	0.033
LE	1.10	1.50	0.043	0.059
М	0 °	10 °	0 °	10 °
Q <sub>1</sub>	0.70	0.90	0.028	0.035
Z		0.81		0.032



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